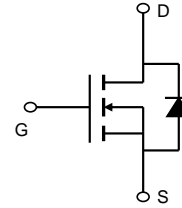


## General Description

- Trench Power MOSFET technology
- Low  $R_{DS(ON)}$  at 10 V<sub>GS</sub>
- Low Gate Charge

## Product Summary

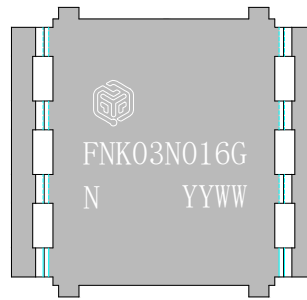
$V_{DS}$	30V
$I_D$ (at $V_{GS}=10V$ )	130A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	< 1.6m $\Omega$



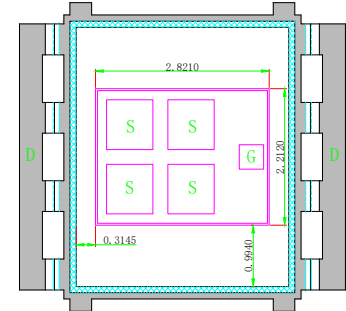
Schematic diagram



Side View



Top View



Bottom View

TDHD4\*5

## Applications

- Load switch, battery switch
- Automotive applications
- Uninterruptible power supply

Orderable Part Number	Package Type	Form	Minimum Order Quantity	
FNK03N016G	TDHD 4*5	Tape & Reel		
<b>Absolute Maximum Ratings</b> $T_A=25^{\circ}C$ unless otherwise noted				
Parameter	Symbol	Maximum	Units	
Drain-Source Voltage	$V_{DS}$	30	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V	
Continuous Drain Current $I_{D,G}$	$I_D$	130	A	
Pulsed Drain Current $I_{DM}^C$	$I_{DM}$	520		
Avalanche energy $L=0.5mH$ $E_{AS}^C$	$E_{AS}$	270	mJ	
Power Dissipation <sup>B</sup>	$P_D$	96	W	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^{\circ}C$	
<b>Thermal Characteristics</b>				
Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	25	30	$^{\circ}C/W$
Maximum Junction-to-Ambient <sup>A,D</sup>		Steady-State	40	50
Maximum Junction-to-Case	$R_{\theta JC}$	1.3	1.8	$^{\circ}C/W$

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±10V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.5	2.5	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =25A		1.3	1.6	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A		2.1	2.5	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =20A		150		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V			1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				50	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz		5100		pF
C <sub>oss</sub>	Output Capacitance			1550		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			220		pF
R <sub>g</sub>	Gate resistance	f=1MHz			3.5	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =20A		80	100	nC
Q <sub>g</sub> (4.5V)	Total Gate Charge			34	54	nC
Q <sub>gs</sub>	Gate Source Charge			11		nC
Q <sub>gd</sub>	Gate Drain Charge			12		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =0.75Ω, R <sub>GEN</sub> =3Ω		8		ns
t <sub>r</sub>	Turn-On Rise Time			7		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			90		ns
t <sub>f</sub>	Turn-Off Fall Time			20		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =20A, di/dt=500A/μs		24		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =20A, di/dt=500A/μs		65		nC

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The Power dissipation P<sub>DSM</sub> is based on R<sub>θJA</sub> ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C.

D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to case R<sub>θJC</sub> and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C.

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

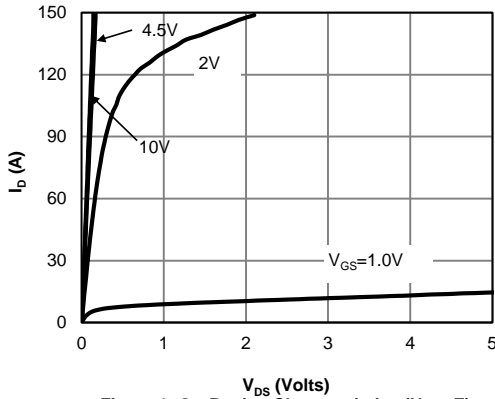


Figure 1: On-Region Characteristics (Note E)

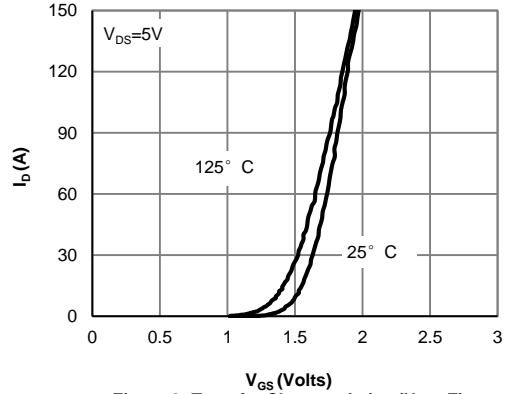


Figure 2: Transfer Characteristics (Note E)

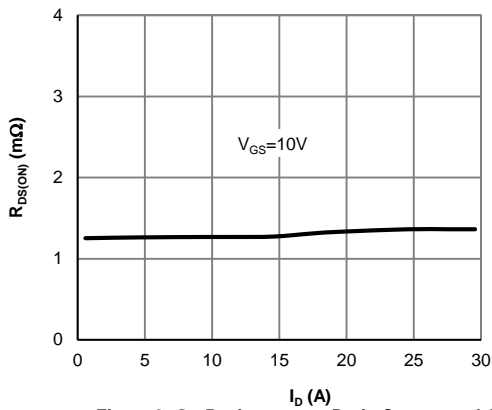


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

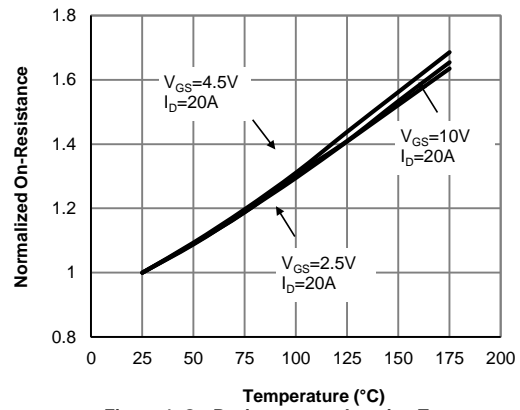


Figure 4: On-Resistance vs. Junction Temperature (Note E)

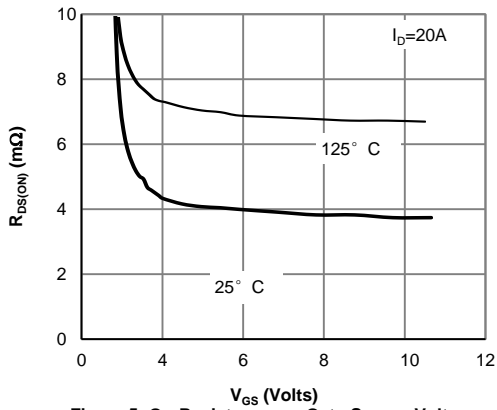


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

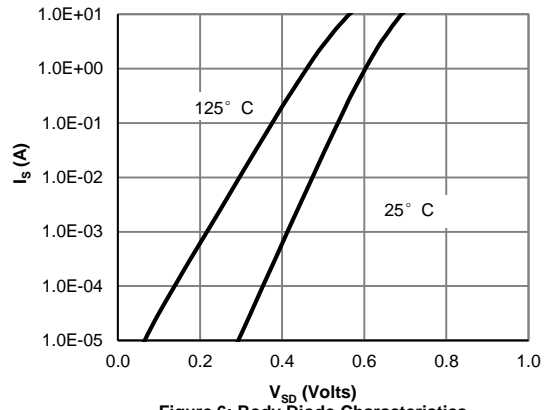


Figure 6: Body-Diode Characteristics (Note E)

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

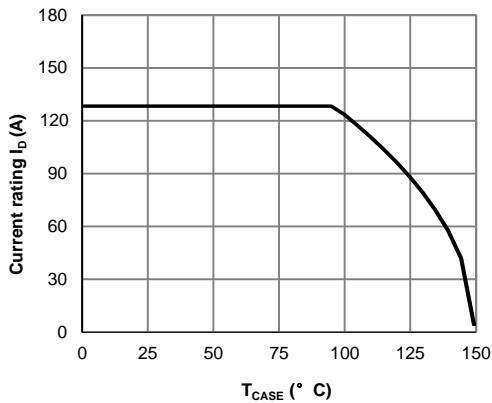


Figure 7: Current De-rating (Note F)

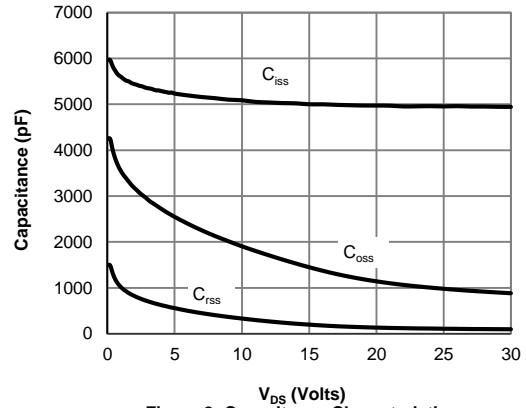


Figure 8: Capacitance Characteristics

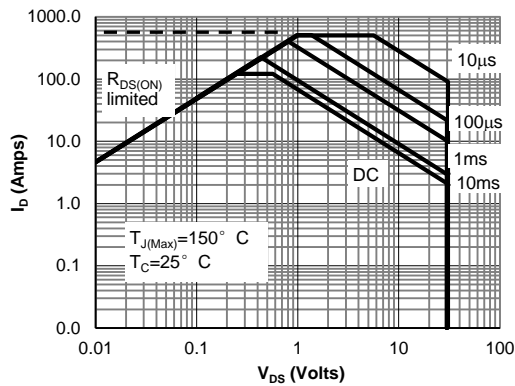


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

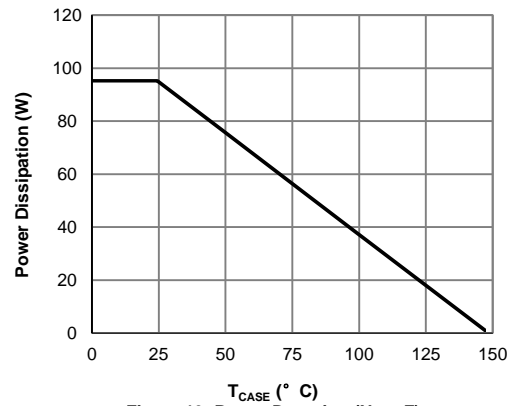


Figure 10: Power De-rating (Note F)

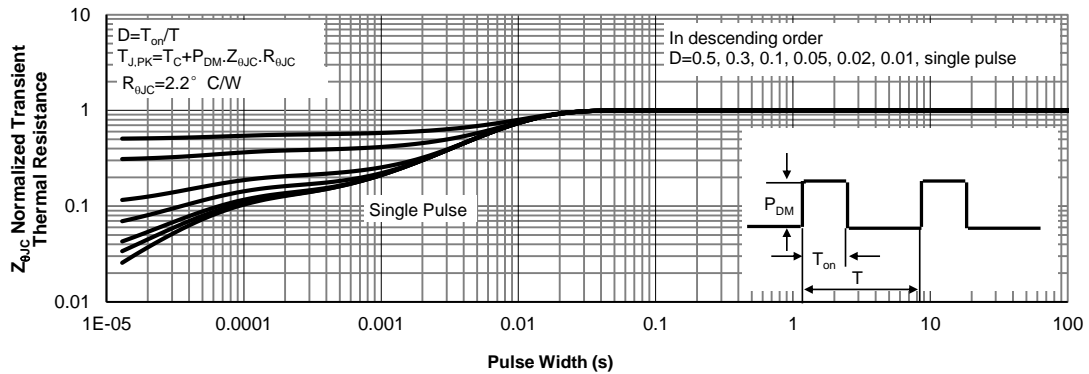


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Figure A: Gate Charge Test Circuit & Waveforms

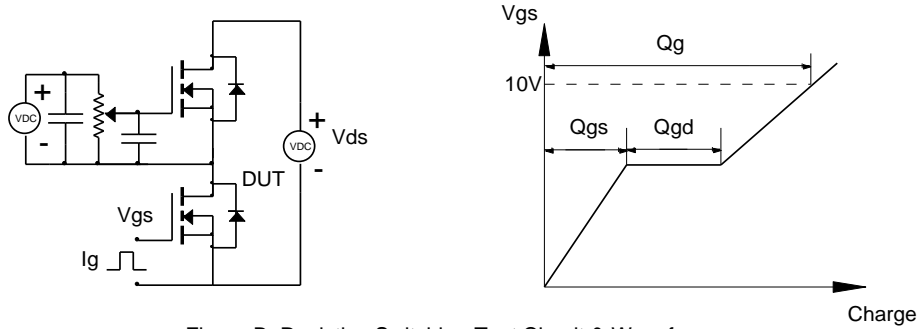


Figure B: Resistive Switching Test Circuit & Waveforms

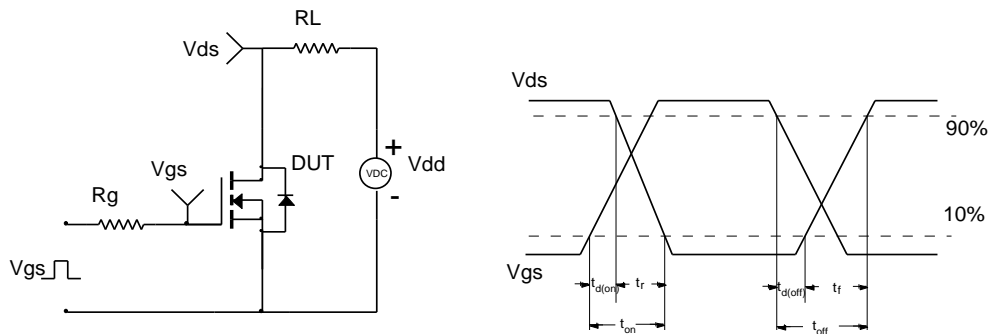


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

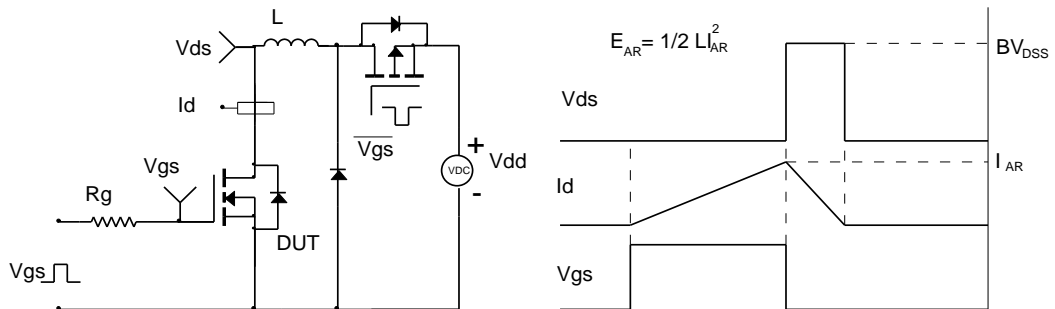
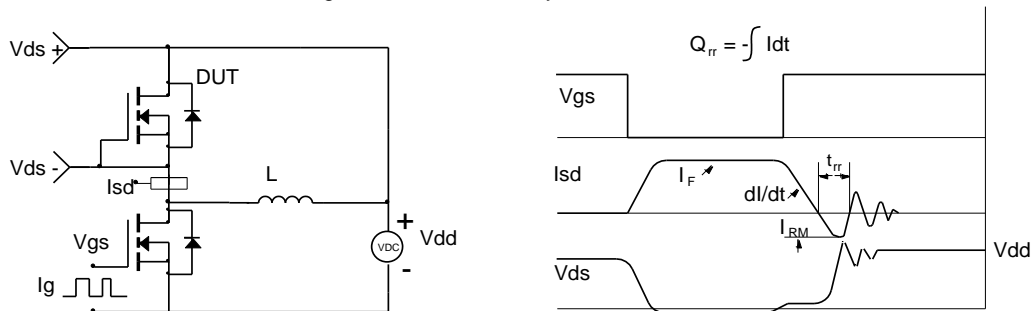
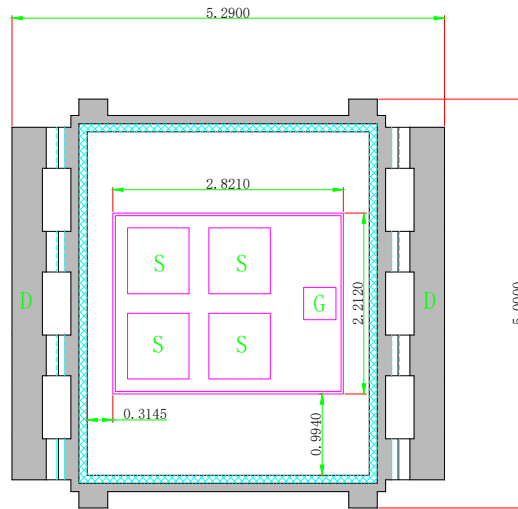


Figure D: Diode Recovery Test Circuit & Waveforms

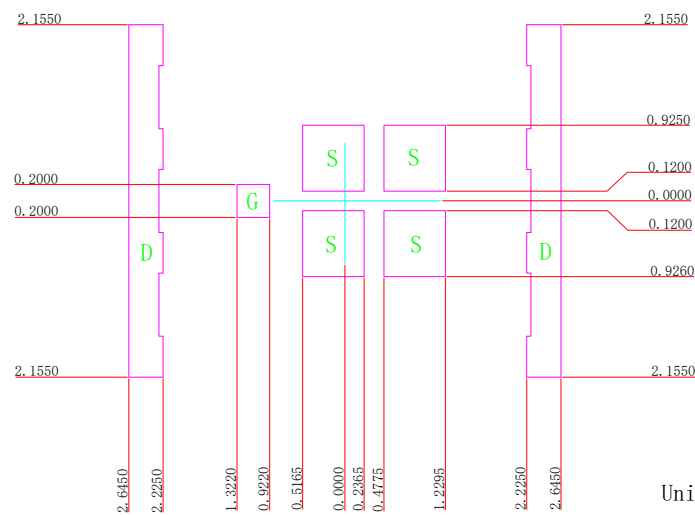


## TDHD5\*6 Package Information

Unit: mm



Back



Unit: mm

Front  
PCB钢网印刷尺寸

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